

Supporting information for

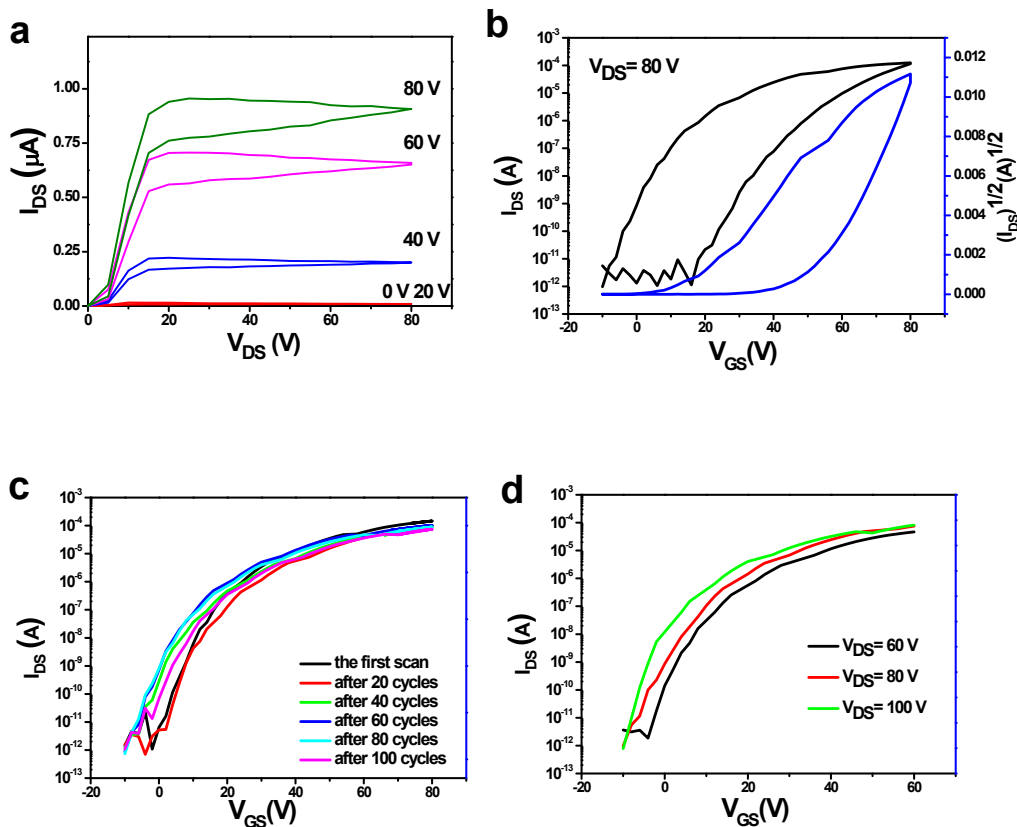
## n-Type organic light-emitting transistors with high mobility and improved air stability

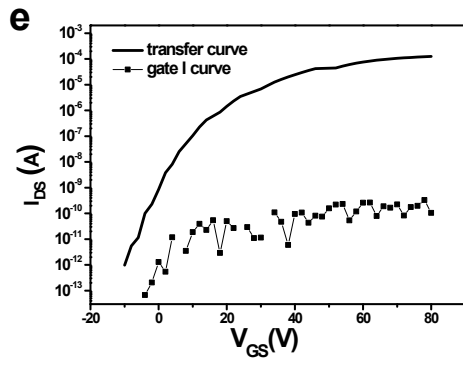
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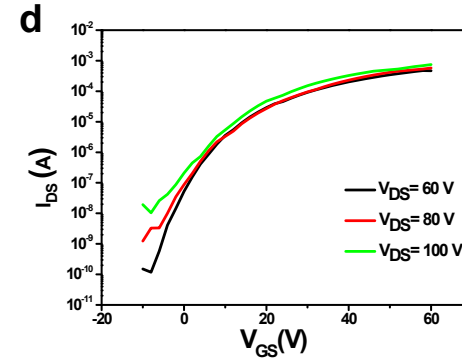
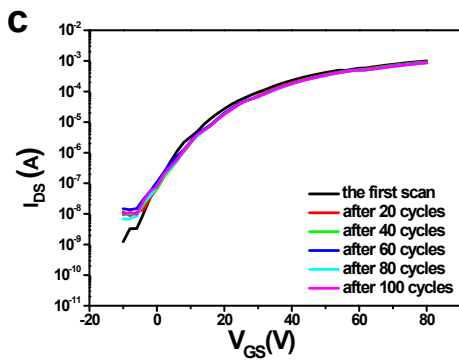
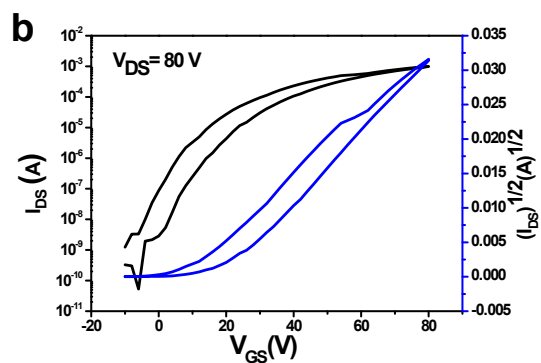
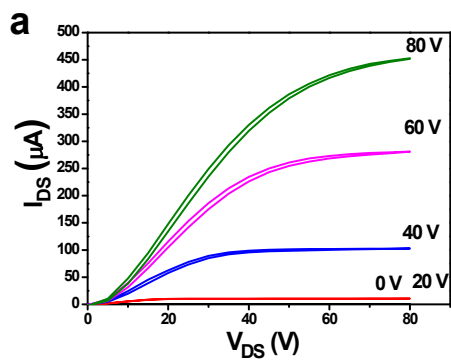
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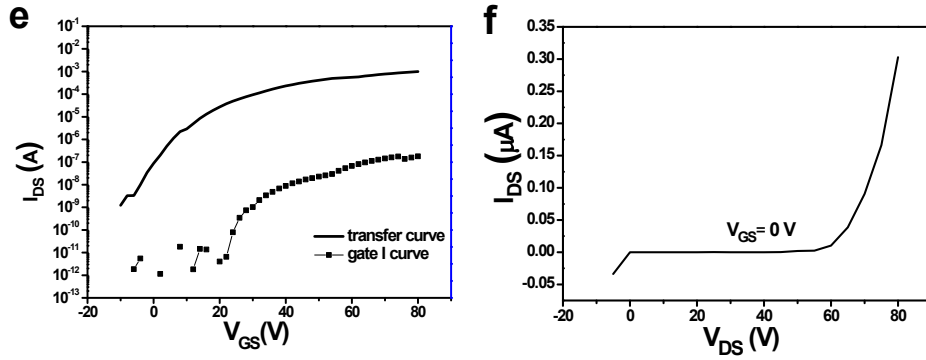
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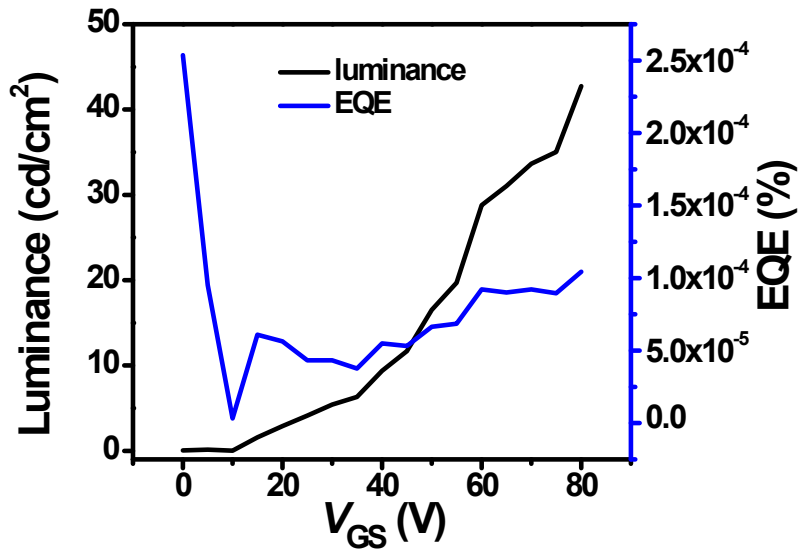


**Fig S1.** (a) Forward and backward scan of output curves. (b) Forward and backward scan of transfer curves. (c) Operation stability measurement. (d) Transfer curve under different  $V_{DS}$ . (e) Gate leakage current for BGBC OTFTs without thermal treatment in air





**Fig S2.** (a) Forward and backward scan of output curves. (b) Forward and backward scan of transfer curves. (c) Operation stability measurement. (d) Transfer curve under different  $V_{DS}$ . (e) Gate leakage current. (f) Single string of output curves at  $V_{GS} = 0$  V for BGBC OTFTs with thermal annealing at 180 °C in air



**Fig. S3.** Curves of luminance and EQE vs.  $V_{GS}$ .

1. Calculating EQE based on EL spectrum

In an EL spectrum, the intensity in unit of  $s^{-1} nm^{-1}$  ( $I_1$ ) at a given wavelength ( $\lambda$  in

nm) is recorded. Thus, the intensity in unit of  $W\ nm^{-1}$  ( $I_2$ ) at the same wavelength is given by

$$I_2 = I_1 \times \frac{1240}{\lambda} \times 1.6 \times 10^{-19}. \quad (1)$$

The total radiant power in W ( $I_3$ ) of the emitted light can be obtained via integrating the  $I_2$  over the EL spectrum, expressed as

$$I_3 = k \int I_2 d\lambda. \quad (2)$$

Incorporating Eq. 1 into Eq. 2, one can obtain

$$I_3 = k \int I_1 \times \frac{1240}{\lambda} \times 1.6 \times 10^{-19} d\lambda. \quad (3)$$

Because the  $I_1$ ,  $I_3$ , and  $\lambda$  are known, the  $k$  is then calculated. The total photon flux in  $s^{-1}$  ( $I_4$ ) of the emitted light can be obtained via integrating the  $I_1$  over the EL spectrum, expressed as

$$I_4 = k \int I_1 d\lambda. \quad (4)$$

The number of electrons ( $N$  in  $s^{-1}$ ) flowing through the loop is given by dividing the current ( $I$  in A) by the electric charge of one electron. Then, the EQE is obtained by dividing the  $I_4$  by the  $N$ .

## 2. Calculating luminance ( $L$ in $cd/m^2$ ) based on the EL spectrum

Mathematically, for a given EL spectrum, the luminous flux quantity (LF in lm) of the emitted light is given by

$$LF = k \int I_2 \times P_H d\lambda, \quad (5)$$

where the  $P_H$  is the photopic luminous efficiency. Assuming the emissive area (Area in  $m^2$ ) to be a lambertian source, the  $L$  is given by

$$L = \frac{LF}{\pi \times Area}. \quad (6)$$

The light emitting region is estimated as 1 nm near the electrode.

**Reference:**

- [1] D. S. Qin, Y. Tao, *Appl. Phys. Lett.* 2005, **86**, 113507.